L Number	Hits	Search Text	DB	Time stamp
-	909	((mold near2 (upper lower)) and	USPAT;	2004/01/26
		semiconductor and (chip die wafer)) and (methor process)	US-PGPUB; EPO; JPO; DERWENT	10:15
_	468	(((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (methor process)) and (inject injecting	USPAT; US-PGPUB; EPO; JPO;	2002/09/20 09:57
_	403	injected) ((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (methor process)) and (inject injecting	DERWENT USPAT; US-PGPUB; EPO; JPO;	2002/09/20 09:58
_	1	injected)) and (resin encapsulant sealing)	DERWENT USPAT;	2002/09/20
		semiconductor and (chip die wafer)) and (methor process)) and (inject injecting injected)) and (resin encapsulant sealing)) and ((releasable released releasing) nearl (layer film material))	US-PGPUB; EPO; JPO; DERWENT	10:08
_	101		USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 10:03
-	63	<pre>((((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (methor process)) and (inject injecting injected)) and (resin encapsulant sealing)) and (releasable released releasing)) and ((flipchip (flip adj</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 11:06
-	179	chip)) bump ball) (mold near2 (upper lower)) and ((releasable released releasing) near1 (layer film material))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 10:10
_	12	((mold near2 (upper lower)) and ((releasable released releasing) near1 (layer film material))) and semiconductor and (chip die wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 10:27
_	0	6123895. URPN.	USPAT	2002/09/20 10:16
_	5	("3178807" "5006417" "5384087" "5616421" "5902943").PN.	USPAT	2002/09/20
_		jp408142106a	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 10:29
-	156	MIYAJIMA-FUMIO	USPAT; US-PGPUB; EPO; JPO;	2002/09/20 10:30
-	19	MIYAJIMA-FUMIO	DERWENT USPAT; EPO	2002/09/20 10:30
-	1	6187243.pn. and (parting adj face)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/20 14:01
-	1481	(mold near2 (upper lower)) and semiconductor and (chip die wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/08 09:42
-	39173	mold near2 (upper lower)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 09:34

-	54	(mold near2 (upper lower)) near3 (air adj vent)	USPAT; US-PGPUB;	2002/09/24 14:59
_	8	((mold near2 (upper lower)) near3 (air adj vent)) and semiconductor and (chip	EPO; JPO; DERWENT USPAT; US-PGPUB;	2002/09/24
_	5628	die wafer) tab near3 lead	EPO; JPO; DERWENT USPAT;	2002/09/24
	3020	tab hears read	US-PGPUB; EPO; JPO; DERWENT	15:18
_	1951	(tab near3 lead) and semiconductor and (chip die wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 08:33
	92	((tab near3 lead) and semiconductor and (chip die wafer)) and ((lead near3 (plated plating electroplated electroplating)) with (electrode terminal pad))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 08:34
-	21		USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/09/24 15:29
_	3900	257/787	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/12 12:29
_	1339	257/787 and shape	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/12 12:29
_	57	(257/787 and shape) and leadless	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/02/12 12:29
_	40537	mold near2 (upper lower)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/08 09:40
. _	7365	(mold near2 (upper lower)) and (chip die wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 09:37
	4354	((mold near2 (upper lower)) and (chip die wafer)) and (methor process)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 09:39
_	5701	((mold near2 (upper lower)) and (chip die wafer)) and (method process)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 09:39
- .	173	<pre>(((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj chip))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 09:45
	0	<pre>((((mold near2 (upper lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj chip))) and ((releasable released releasing) near (film layer tape))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 11:07
-	12		USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/27 14:36
_	0	20020017738.URPN.	USPAT	2003/03/27 12:20

_	55	((((mold near2 (upper lower)) and (chip	USPAT;	2003/03/27
		die wafer)) and (method process)) and	US-PGPUB;	14:35
		(flipchip (flip adj chip))) and	EPO; JPO;	
_	43	<pre>(releasable released release releasing) (((((mold near2 (upper lower)) and (chip</pre>	DERWENT USPAT;	2003/03/27
		die wafer)) and (method process)) and	US-PGPUB;	12:24
		(flipchip (flip adj chip))) and	EPO; JPO;	
		<pre>(releasable released release releasing)) not (((((mold near2 (upper lower)) and</pre>	DERWENT	
		(chip die wafer)) and (method process))		
		and (flipchip (flip adj chip))) and		
		((releasable released release releasing)		
_	98	near (film layer tape))) 5450283.URPN.	USPAT	2003/03/27
			052112	14:35
-	759		USPAT	2003/03/27
		die wafer)) and (method process)) and (bump ball)		14:35
_	671	((((mold near2 (upper lower)) and (chip	USPAT	2003/03/27
		die wafer)) and (method process)) and		14:35
		(bump ball)) not (((mold near2 (upper		
		lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj		
		chip)))		
-	275		USPAT;	2003/03/27
		<pre>die wafer)) and (method process)) and (bump ball)) not ((((mold near2 (upper</pre>	US-PGPUB; EPO; JPO;	14:36
		lower)) and (chip die wafer)) and	DERWENT	
		(method process)) and (flipchip (flip adj		
		<pre>chip)))) and (releasable released release releasing)</pre>		
-	10		USPAT;	2003/03/27
		die wafer)) and (method process)) and	US-PGPUB;	14:43
		(bump ball)) not ((((mold near2 (upper lower)) and (chip die wafer)) and	EPO; JPO; DERWENT	
		(method process)) and (flipchip (flip adj	DERWENT	
		chip)))) and ((releasable released		
		release releasing) nearl (film layer tape))		
_	2	6019588.URPN.	USPAT	2003/03/27
				14:41
-	16	("4044984" "4236689" "4332537" "4442056" "4470786" "4697784"	USPAT	2003/03/27
	Ī	"4779835" "5059105" "5118271"		14:41
		"5218759" "5429488" "5484274"		
		"5626886" "5639695" "5693572" "5779958"\ DN		
_	265	"5779958").PN. (((((mold near2 (upper lower)) and	USPAT;	2003/03/27
		<pre>(chip die wafer)) and (method process))</pre>	US-PGPUB;	14:43
		and (bump ball)) not ((((mold near2	EPO; JPO;	
		<pre>(upper lower)) and (chip die wafer)) and (method process)) and (flipchip (flip adj</pre>	DERWENT	
		<pre>chip)))) and (releasable released release</pre>		
		releasing)) not (((((mold near2 (upper		
		<pre>lower)) and (chip die wafer)) and (method process)) and (bump ball)) not</pre>		
		((((mold near2 (upper lower)) and (chip		
		die wafer)) and (method process)) and		
		<pre>(flipchip (flip adj chip)))) and ((releasable released release releasing)</pre>		
		near1 (film layer tape)))		
-	1	"20030052418"	USPAT;	2003/05/08
			US-PGPUB;	09:32
			EPO; JPO; DERWENT	
_	40999	mold near2 (upper lower)	USPAT;	2003/05/08
			US-PGPUB;	09:41
	.		EPO; JPO; DERWENT	
			NEI/MEI/I	

_	1694	(mold near2 (upper lower)) and semiconductor and (chip die wafer)	USPAT; US-PGPUB; EPO; JPO;	2004/01/26 10:15
-	446	((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (leadframe (lead near1 (inner outer)))	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/05/08 09:45
-	395	(((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and	DERWENT USPAT; US-PGPUB;	2003/05/08 12:18
		(leadframe (lead nearl (inner outer)))) and (sealing sealed encapsulant encapsulating encapsulated)	EPO; JPO; DERWENT	
-	369	<pre>((((mold near2 (upper lower)) and semiconductor and (chip die wafer)) and (leadframe (lead near1 (inner outer)))) and (sealing sealed encapsulant</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/26 10:17
_	122		USPAT;	2003/05/08
		semiconductor and (chip die wafer)) and (leadframe (lead nearl (inner outer)))) and (sealing sealed encapsulant encapsulating encapsulated)) and (method	US-PGPUB; EPO; JPO; DERWENT	09:47
-	53	process)) and ((die mounting) adj pad) 5474958.URPN.	USPAT	2003/05/08 09:52
_	0	6472252.URPN.	USPAT	2003/05/08 09:59
-	36	("4313718" "4697784" "4881884" "4944908" "5147821" "5355283" "5362679" "5405255" "5406699" "5467253" "5468999" "5474958" "5477611" "5479051" "5490324" "5506756" "5508565" "5527743" "5543658" "5545922" "5556807" "5596227" "5609889" "5626886" "5656549" "5663106" "5665281" "5688716" "5766649" "5766650" "5817545" "5876765" "5923959" "5928595" "6117382" "6281588").PN.	USPAT	2003/05/08 09:59
_	3	6117382.URPN.	USPAT	2003/05/08 10:01
-	20	("5034350" "5114880" "5147815" "5222014" "5239806" "5313365" "5331205" "5366364" "5458694" "5488257" "5578261" "5597643" "5598034" "5608262" "5609889" "5614441" "5615089" "5646829" "5755914" "5830781").PN.	USPAT	2003/05/08
-	20	("5034350" "5114880" "5147815" "5222014" "5239806" "5313365" "5331205" "5366364" "5458694" "5488257" "5578261" "5597643" "5598034" "5608262" "5609889" "5614441" "5615089" "5646829" "5755914" "5830781").PN.	USPAT	2003/05/08 10:04
-	7	5923959.URPN.	USPAT	2003/05/08 10:05
-	20	("5355283" "5362679" "5406699" "5467253" "5468999" "5474958" "5477611" "5479051" "5490324" "5506756" "5508565" "5527743" "5543658" "5545922" "5556807" "5596227" "5609889" "5656549" "5663106" "5688716").PN.	USPAT	2003/05/08 10:10
-	21	5609889.URPN.	USPAT	2003/05/08 10:12
-	0	6428300.URPN.	USPAT	2003/05/08 10:13

-	29	("3505446" "3685784" "3991146"	USPAT	2003/05/08
		"4184835" "4464322" "4470786"		10:13
		"4618466" "4770833" "4954308"		
		"5049344" "5049526" "5110515"		
		"5174941" "5326243" "5344600"		
		"5366368" "5429488" "5451153"		
		"5480296" "5523038" "5558883"		l
		"5609889" "5626886" "5650177"		
		"5714106" "5798070" "5989471"		
	0.5	"6030569" "6224360").PN.		2222 (25 (22
-	26	5817545.URPN.	USPAT	2003/05/08
		CEEOOOO WADAY		10:18
-	0	6558982.URPN.	USPAT	2003/05/08
		/#5017545# #5074334# #5000343#	II.C.D.N.M.	10:19
-	6	("5817545" "5874324" "5998243" "6204095" "6329224" "6335221").PN.	USPAT	2003/05/08
	36	("3930114" "4043027" "4437141"	HCDAM	10:19
-	36	(3930114	USPAT	2003/05/08
		"4688152" "4778641" "4823234"		10:23
		"4859722" "4861251" "4868349"		, i
		"4890152" "4893172" "4935581"		
	i	"4954877" "4954878" "4961105"		
		"4972253" "4975765" "5019673"		
I		"5049526" "5093282" "5108955"		
1		"5132778" "5136366" "5153385"		
		"5191511" "5216278" "5218759"		
		"5241133" "5296738" "5328870"		
	ľ	"5355283" "5370517" "5395226").PN.		
-	40	5108955.URPN.	USPAT	2003/05/08
				10:26
-	7	("4266239" "4541005" "4778641"	USPAT	2003/05/08
		"4822550" "4823234" "4868638"		10:43
		"4890152").PN.		
-	3	6081978.URPN.	USPAT	2003/05/08
	1			12:10
-	3	("5336272" "6001671" "6033933").PN.	USPAT	2003/05/08
				12:11
-	113	((((mold near2 (upper lower)) and	USPAT;	2003/05/08
		semiconductor and (chip die wafer)) and	US-PGPUB;	12:18
		(leadframe (lead near1 (inner outer))))	EPO; JPO;	
		and (sealing sealed encapsulant	DERWENT	
		encapsulating encapsulated)) and (vent		
	200176	vacuum)	HCDAM.	2002/05/09
-	389176	"113" not ((((((mold near2 (upper lower)) and semiconductor and (chip die wafer))	USPAT; US-PGPUB;	2003/05/08 12:19
		and (leadframe (lead nearl (inner	EPO; JPO;	12.19
		outer)))) and (sealing sealed encapsulant	DERWENT	
		encapsulating encapsulated)) and (method	SUMBILI	
		process)) and ((die mounting) adj pad))		
_	91	(((((mold near2 (upper lower)) and	USPAT;	2003/05/08
		semiconductor and (chip die wafer)) and	US-PGPUB;	12:19
		(leadframe (lead near1 (inner outer))))	EPO; JPO;	
		and (sealing sealed encapsulant	DERWENT	
		encapsulating encapsulated)) and (vent		
		vacuum)) not (((((mold near2 (upper		
		lower)) and semiconductor and (chip die		
		wafer)) and (leadframe (lead nearl (inner		
		outer)))) and (sealing sealed encapsulant		
		encapsulating encapsulated)) and (method		
		<pre>process)) and ((die mounting) adj pad))</pre>		<u> </u>
-	25	5147821.URPN.	USPAT	2003/05/08
	_			12:24
-	2	("4866506" "4944908").PN.	USPAT	2003/05/08
		5147001 27702		12:26
_	25	5147821.URPN.	USPAT	2003/05/08
_		E 4740E 9 TIDDN	IIC DAM	13:43
-	53	5474958.URPN.	USPAT	2003/05/08 13:44
_	4	5776800.URPN.	TIEDAT	2003/05/08
-	4	3//0000.URFN.	USPAT	13:45
			i	

13:45		5	("5101324" "5130889" "5309026"	USPAT	2003/05/08
13:48			"5394298" "5474958").PN.		13:45
-	-	2	5874319.URPN.	USPAT	
-	_	21	"4932883" "5147821" "5173451" "5203401" "5237269" "5322207" "5336649" "5367253" "5378981" "5424652" "5459351" "5474958" "5475317" "5489538" "5548884"	USPAT	2003/05/08
-	-	2		USPAT	
S "6081978" USPAT; US-PGPUB; EPO: JPO: DERWENT USPAT: USP	-	2	("4866506" "4944908").PN.	USPAT	2003/05/08
-	-	5	"6081978"	US-PGPUB;	2003/05/12
T40	-	3	("5336272" "6001671" "6033933").PN.	DERWENT	
A71	-	740	(memory adj chip) near3 array	US-PGPUB;	2003/05/12
137	-	471		DERWENT USPAT; US-PGPUB; EPO; JPO;	
-	-	137		USPAT; US-PGPUB; EPO; JPO;	1
- 1406 (memory near chip) near4 array USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT; USPAT	-	8		USPAT; US-PGPUB; EPO; JPO;	1
- 15 ((memory near chip) near4 array) with known USPAT; US-PGPUB; EPO; JPO; DERWENT	-	1406	(memory near chip) near4 array	USPAT; US-PGPUB; EPO; JPO;	7
7 (((memory near chip) near4 array) with known) not (((memory adj chip) near3 array) with known) 2102 (tab near3 lead) and semiconductor and (chip die wafer) 1640 ((tab near3 lead) and semiconductor and (chip die wafer)) and (lead with (electrode bump ball terminal pad)) 17 (((memory near chip) near4 array) with USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT;	-	15		USPAT; US-PGPUB; EPO; JPO;	
- 2102 (tab near3 lead) and semiconductor and (chip die wafer) - 1640 ((tab near3 lead) and semiconductor and (chip die wafer)) and (lead with (electrode bump ball terminal pad)) Comparison of the compariso	-	7	known) not (((memory adj chip) near3	USPAT; US-PGPUB; EPO; JPO;	
- 1640 ((tab near3 lead) and semiconductor and (chip die wafer)) and (lead with (electrode bump ball terminal pad)) Compared to the compar	-	2102		USPAT; US-PGPUB; EPO; JPO;	
	_	1640	(chip die wafer)) and (lead with	USPAT; US-PGPUB; EPO; JPO;	, ,
((chip die wafer)) and (lead with (S-PGPUB; (electrode bump ball terminal pad))) and (EPO; JPO; (conductive nearl (vias (through adj hole)))	-	123	<pre>(electrode bump ball terminal pad))) and (conductive nearl (vias (through adj</pre>	USPAT; US-PGPUB; EPO; JPO;	2004/01/26 10:18
- 94 ((((tab near3 lead) and semiconductor and (chip die wafer)) and (lead with (electrode bump ball terminal pad))) and EPO; JPO; (conductive near1 (vias (through adj hole)))) and (seal sealed sealing encapsulant encapsulated encapsulating)	-	94	<pre>((((tab near3 lead) and semiconductor and (chip die wafer)) and (lead with (electrode bump ball terminal pad))) and (conductive near1 (vias (through adj hole)))) and (seal sealed sealing</pre>	US-PGPUB; EPO; JPO;	

-	43	(((((tab near3 lead) and semiconductor and (chip die wafer)) and (lead with	USPAT; US-PGPUB;	2003/05/19 08:38
		(electrode bump ball terminal pad))) and	EPO; JPO;	
		(conductive near1 (vias (through adj	DERWENT	
		hole)))) and (seal sealed sealing		
		encapsulant encapsulated encapsulating))		
	1916	and (stacked stacking)		2004/01/26
_	1916	(mold near2 (upper lower)) and semiconductor and (chip die wafer)	USPAT; US-PGPUB;	10:15
		Semiconductor and (chip die water)	EPO; JPO;	10.13
			DERWENT	
_	1562	((mold near2 (upper lower)) and	USPAT;	2004/01/26
		semiconductor and (chip die wafer)) and	US-PGPUB;	10:16
		(method process)	EPO; JPO;	
			DERWENT	<u> </u>
-	430	(((mold near2 (upper lower)) and	USPAT;	2004/01/26
	•	semiconductor and (chip die wafer)) and	US-PGPUB;	10:17
1	,	(method process)) and (leadframe (lead	EPO; JPO;	
		nearl (inner outer))) and (sealing sealed encapsulant encapsulating encapsulated)	DERWENT	
_	232		USPAT;	2004/01/26
		semiconductor and (chip die wafer)) and	US-PGPUB;	10:22
		(method process)) and (leadframe (lead	EPO; JPO;	" "
		nearl (inner outer))) and (sealing sealed	DERWENT	
		encapsulant encapsulating encapsulated))]
		and (vias (through adj hole))		
-	49	(((((mold near2 (upper lower)) and	USPAT;	2004/01/26
		semiconductor and (chip die wafer)) and (method process)) and (leadframe (lead	US-PGPUB;	10:22
		nearl (inner outer))) and (sealing sealed	EPO; JPO; DERWENT	
		encapsulant encapsulating encapsulated))	DERWENT	,
		and (vias (through adj hole))) and		
		((reducing near1 thickness) thinning)		
-	129		USPAT;	2004/01/26
		semiconductor and (chip die wafer)) and	US-PGPUB;	10:22
		(method process)) and (leadframe (lead	EPO; JPO;	
		near1 (inner outer))) and (sealing sealed	DERWENT	
		<pre>encapsulant encapsulating encapsulated)) and (stacked stacking)</pre>		
-	77	(((((mold near2 (upper lower)) and	USPAT;	2004/01/26
		semiconductor and (chip die wafer)) and	US-PGPUB;	10:22
		(method process)) and (leadframe (lead	EPO; JPO;	
		nearl (inner outer))) and (sealing sealed	DERWENT	
		encapsulant encapsulating encapsulated))		
		and (stacked stacking)) and (vias		
_	45	(through adj hole)) ((((((mold near2 (upper lower)) and	USPAT;	2004/01/26
	43	semiconductor and (chip die wafer)) and	US-PGPUB;	10:22
		(method process)) and (leadframe (lead	EPO; JPO;	
		nearl (inner outer))) and (sealing sealed	DERWENT	
		encapsulant encapsulating encapsulated))		
		and (stacked stacking)) and (vias		
		(through adj hole))) not (((((mold near2		
		<pre>(upper lower)) and semiconductor and (chip die wafer)) and (method process))</pre>		
		and (leadframe (lead near1 (inner		
		outer))) and (sealing sealed encapsulant		
		encapsulating encapsulated)) and (vias	•	
		(through adj hole))) and ((reducing near)		
		thickness) thinning))		